

MOSFET – N-Channel, UniFET™

250 V, 33 A, 94 mΩ

FDPF33N25T

Description

UniFET MOSFET is onsemi's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.

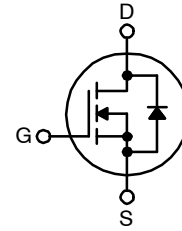
Features

- $R_{DS(on)} = 94 \text{ m}\Omega$ (Max.) @ $V_{GS} = 10 \text{ V}$, $I_D = 16.5 \text{ A}$
- Low Gate Charge (Typ. 36.8 nC)
- Low C_{rss} (Typ. 39 pF)
- 100% Avalanche Tested

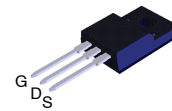
Applications

- PDP TV
- Lighting
- Uninterruptible Power Supply
- AC-DC Power Supply

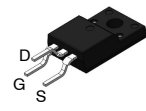
V_{DSS}	$R_{DS(on)} \text{ MAX}$	$I_D \text{ MAX}$
250 V	94 mΩ @ 10 V	33 A



N-Channel MOSFET

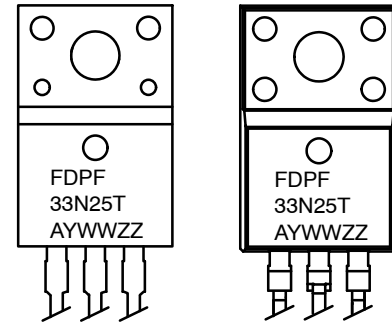


TO-220 Fullpack,
3-Lead /
TO-220F-3SG
CASE 221AT



TO-220-3LD LF
(LG-formed)
CASE 340BL

MARKING DIAGRAM



FDPF33N25T = Specific Device Code
A = Assembly Location
YWW = Date Code (Year & Week)
ZZ = Assembly Lot

ORDERING INFORMATION

See detailed ordering and shipping information on page 3 of this data sheet.

FDPF33N25T

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Symbol	Parameter		FDPF33N25T FDPF33N25TRDTU	Unit
V _{DSS}	Drain–Source Voltage		250	V
I _D	Drain Current	– Continuous (T _C = 25°C) – Continuous (T _C = 100°C)	33* 20.4*	A A
I _{DM}	Drain Current	– Pulsed (Note 1)	132*	A
V _{GSS}	Gate–Source Voltage		±30	V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		918	mJ
I _{AR}	Avalanche Current (Note 1)		33	A
E _{AR}	Repetitive Avalanche Energy (Note 1)		23.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		4.5	V/ns
P _D	Power Dissipation	(T _C = 25°C) – Derate Above 25°C	37 0.29	W W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		–55 to +150	°C
T _L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

*Drain current limited by maximum junction temperature.

1. Repetitive rating: pulse–width limited by maximum junction temperature.
2. L = 1.35 mH, I_{AS} = 33 A, V_{DD} = 50 V, R_G = 25 Ω, starting T_J = 25°C.
3. I_{SD} ≤ 33 A, di/dt ≤ 200 A/μs, V_{DD} ≤ BV_{DSS}, starting T_J = 25°C.

THERMAL CHARACTERISTICS

Symbol	Parameter	FDPF33N25T FDPF33N25TRDTU	Unit
R _{θJC}	Thermal Resistance, Junction–to–Case, Max.	3.4	°C/W
R _{θJA}	Thermal Resistance, Junction–to–Ambient, Max.	62.5	°C/W

FDPF33N25T

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA, T _J = 25°C	250	–	–	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C	–	0.25	–	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 250 V, V _{GS} = 0 V V _{DS} = 200 V, T _C = 125°C	–	–	1 10	μA μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V	–	–	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = –30 V, V _{DS} = 0V	–	–	–100	nA

ON CHARACTERISTICS

V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	3.0	–	5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 16.5 A	–	0.077	0.094	Ω
g _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 16.5 A	–	26.6	–	S

DYNAMIC CHARACTERISTICS

C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz	–	1640	2135	pF
C _{oss}	Output Capacitance		–	330	430	pF
C _{rss}	Reverse Transfer Capacitance		–	39	59	pF

SWITCHING CHARACTERISTICS

t _{d(on)}	Turn-On Delay Time	V _{DD} = 125 V, I _D = 33 A, V _{GS} = 10 V, R _G = 25 Ω (Note 4)	–	35	80	ns
t _r	Turn-On Rise Time		–	230	470	ns
t _{d(off)}	Turn-Off Delay Time		–	75	160	ns
t _f	Turn-Off Fall Time		–	120	250	ns
Q _g	Total Gate Charge	V _{DS} = 200 V, I _D = 33 A, V _{GS} = 10 V (Note 4)	–	36.8	48	nC
Q _{gs}	Gate-Source Charge		–	10	–	nC
Q _{gd}	Gate-Drain Charge		–	17	–	nC

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS

I _S	Maximum Continuous Drain–Source Diode Forward Current		–	–	33	A
I _{SM}	Maximum Pulsed Drain–Source Diode Forward Current		–	–	132	A
V _{SD}	Drain–Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 33 A	–	–	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 33 A, dI _F /dt = 100 A/μs	–	220	–	ns
Q _{rr}	Reverse Recovery Charge		–	1.71	–	μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Essentially independent of operating temperature typical characteristics.

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Mark	Package	Shipping
FDPF33N25T	FDPF33N25T	TO-220 Fullpack, 3-Lead / TO-220F-3SG CASE 221AT	1000 Units / Tube
FDPF33N25TRDTU	FDPF33N25T	TO-220-3LD LF (LG-formed) CASE 340BL	800 Units / Tube

TYPICAL PERFORMANCE CHARACTERISTICS

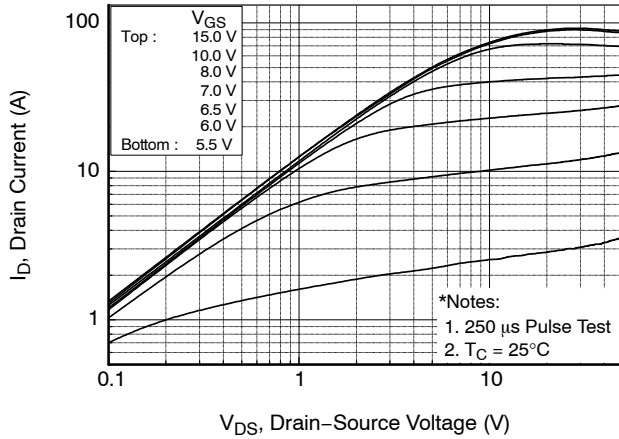


Figure 1. On-Region Characteristics

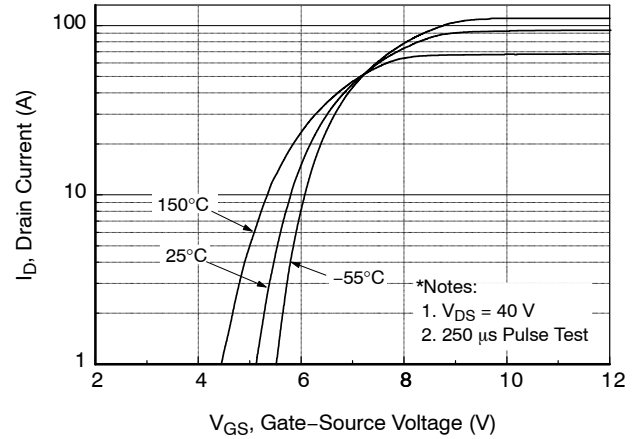


Figure 2. Transfer Characteristics

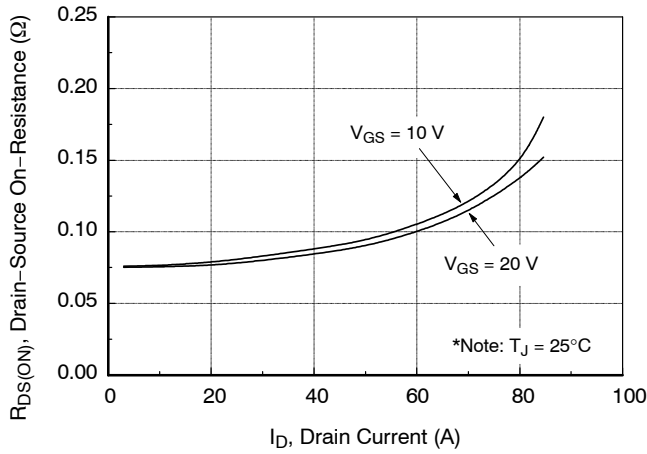


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

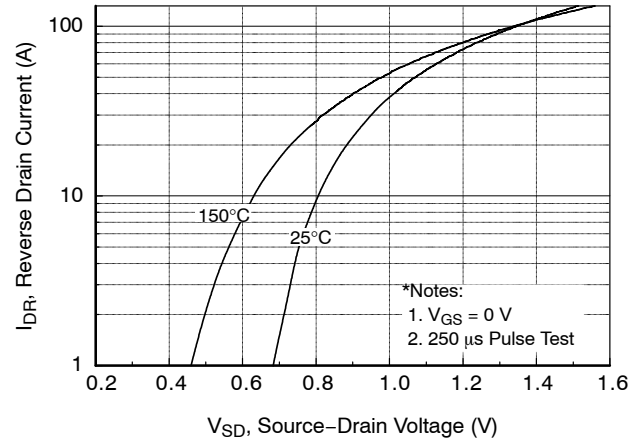


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

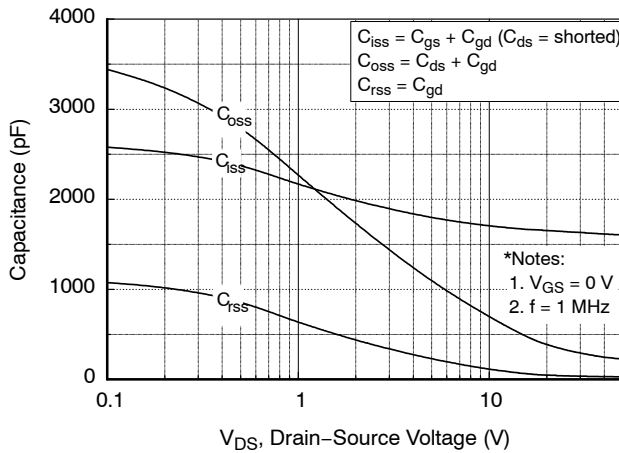


Figure 5. Capacitance Characteristics

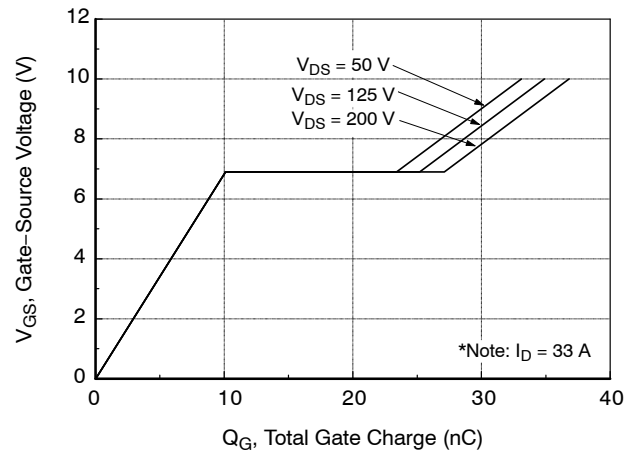


Figure 6. Gate Charge Characteristics

TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

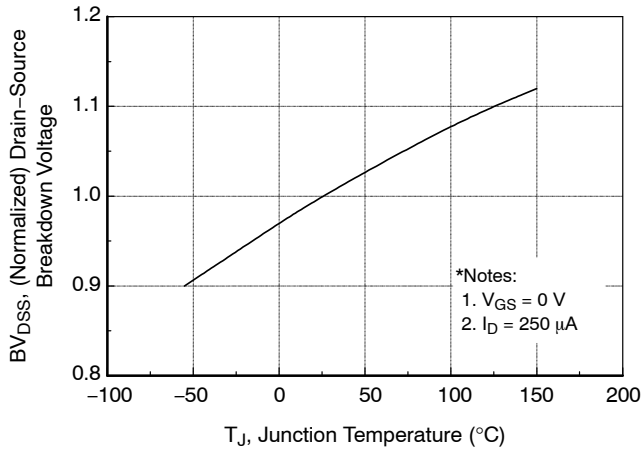


Figure 7. Breakdown Voltage Variation vs. Temperature

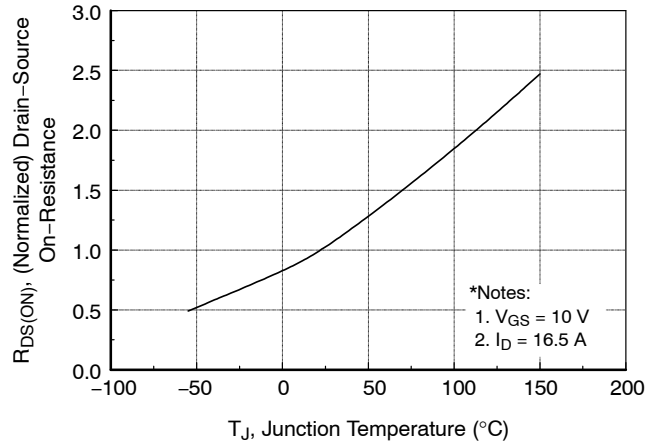


Figure 8. On-Resistance Variation vs. Temperature

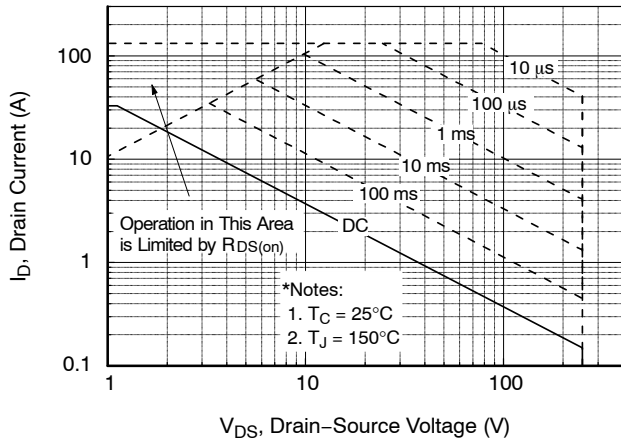


Figure 9. Maximum Safe Operating Area

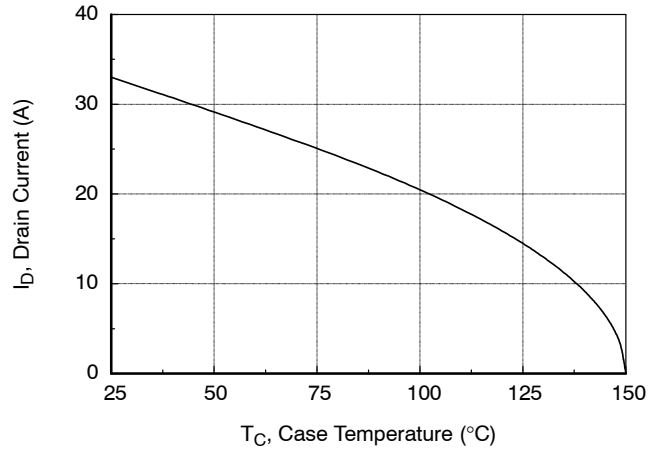


Figure 10. Maximum Drain Current vs. Case Temperature

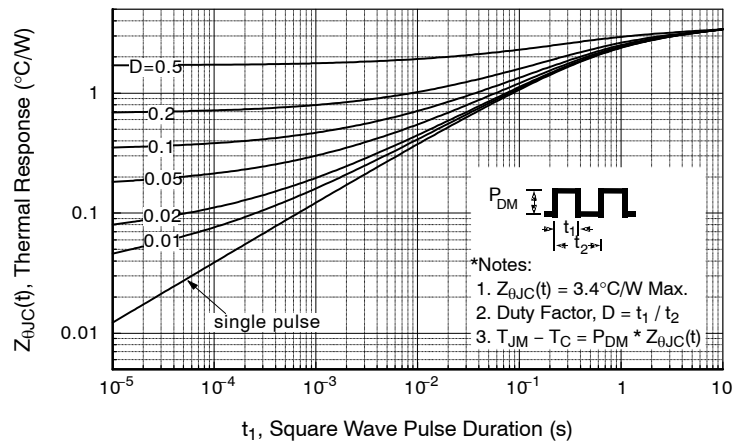
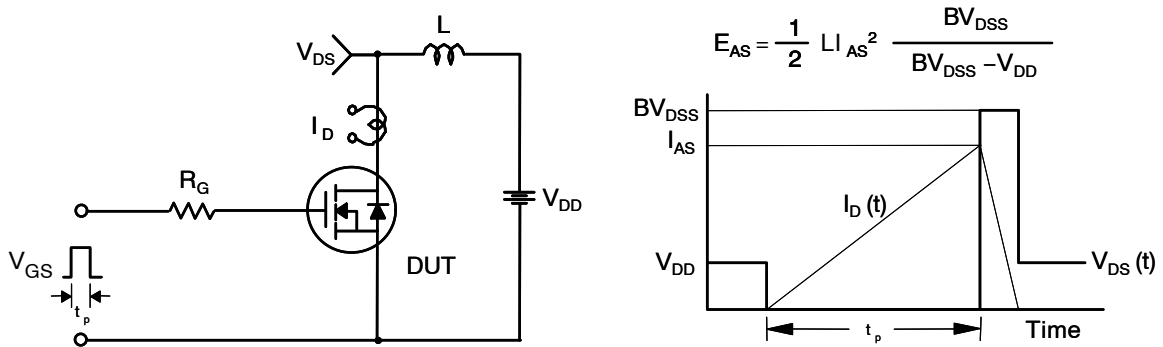
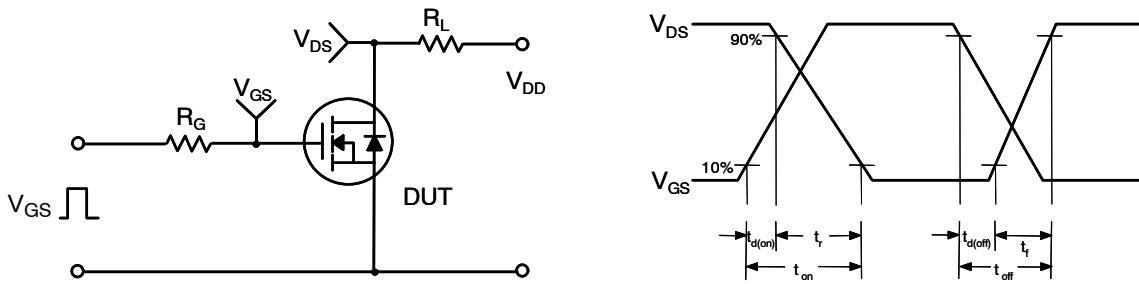
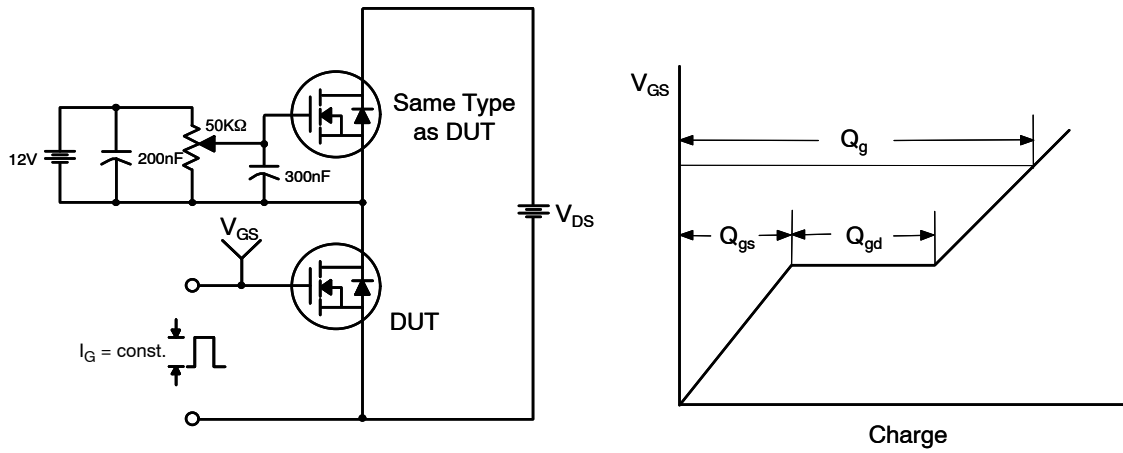


Figure 11. Transient Thermal Response Curve



FDPF33N25T

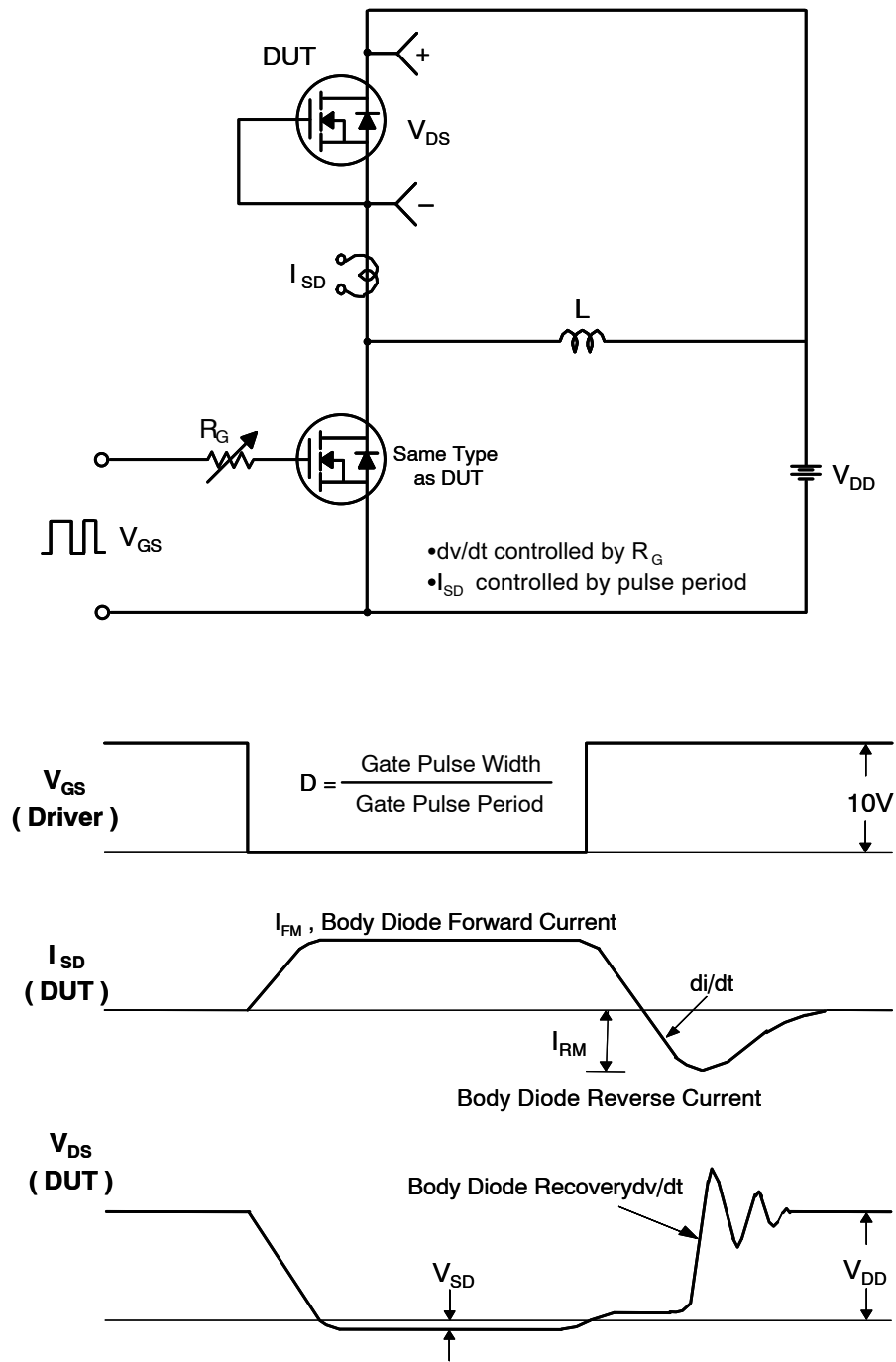
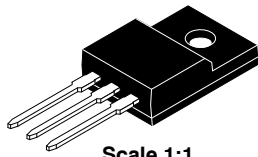


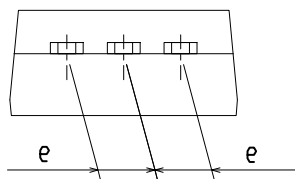
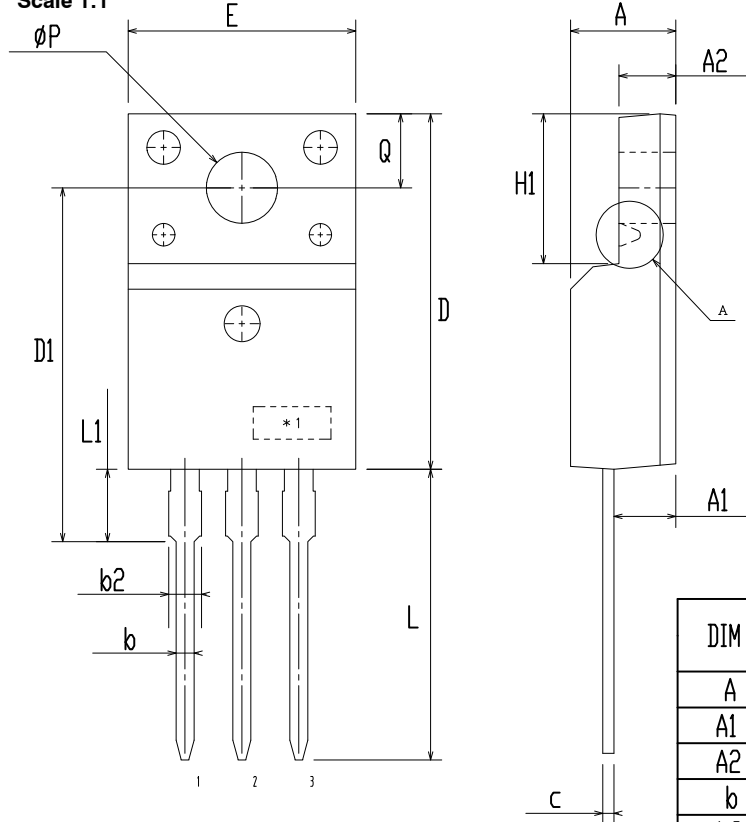
Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

TO-220 Fullpack, 3-Lead / TO-220F-3SG
CASE 221AT
ISSUE B

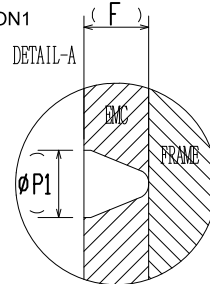
DATE 19 JAN 2021



Scale 1:1



OPTION1



DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.50	4.70	4.90
A1	2.56	2.76	2.96
A2	2.34	2.54	2.74
b	0.70	0.80	0.90
b2	~	~	1.47
c	0.45	0.50	0.60
D	15.67	15.87	16.07
D1	15.60	15.80	16.00
E	9.96	10.16	10.36
e	2.34	2.54	2.74
F	~	0.84	~
H1	6.48	6.68	6.88
L	12.78	12.98	13.18
L1	3.03	3.23	3.43
Ø P	2.98	3.18	3.38
Ø P1	~	1.00	~
Q	3.20	3.30	3.40

NOTES:

A. DIMENSION AND TOLERANCE AS ASME Y14.5-2009

B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUCTIONS.

C. OPTION 1 - WITH SUPPORT PIN HOLE

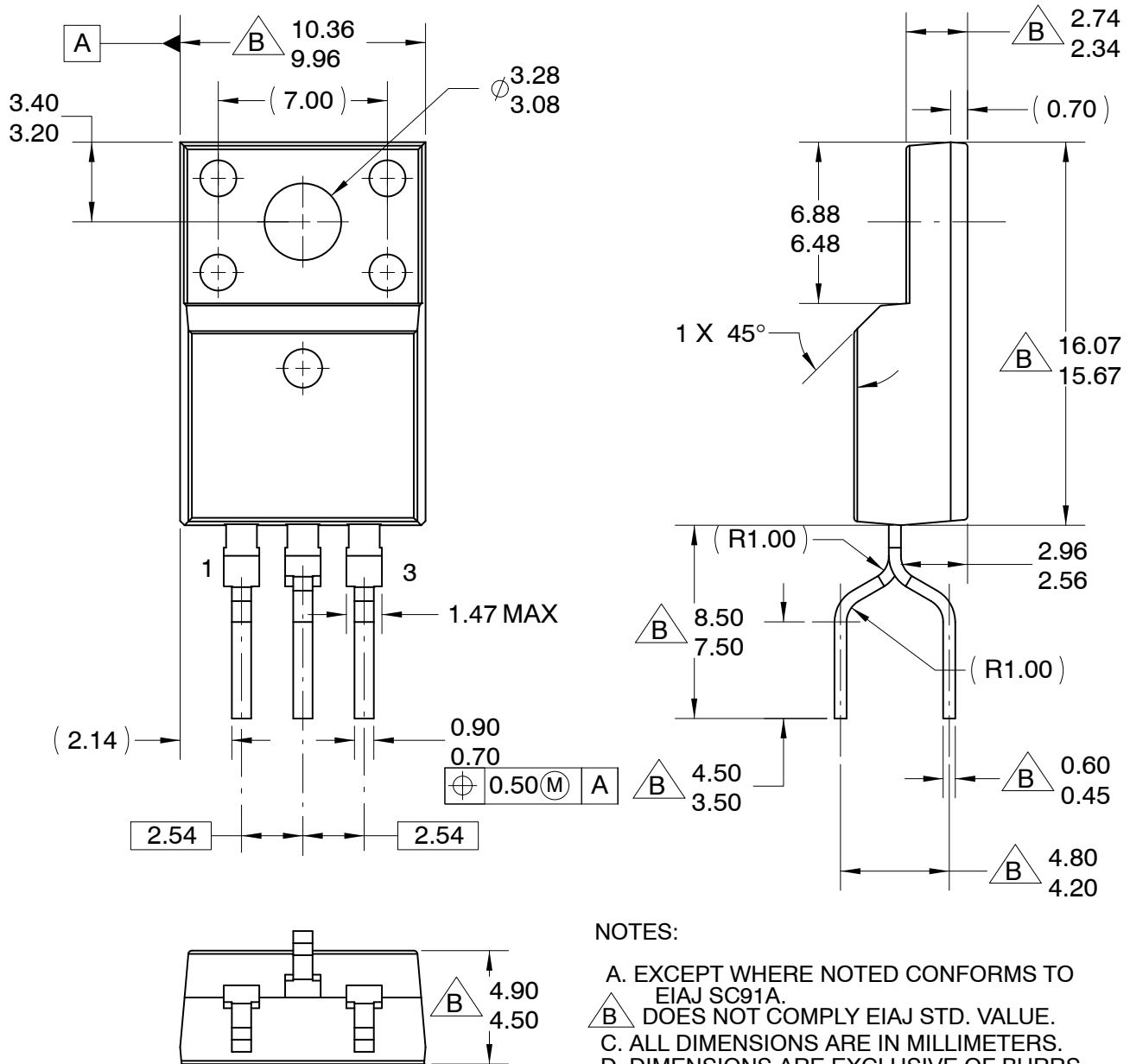
OPTION 2 - NO SUPPORT PIN HOLE

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TO-220-3LD LF
CASE 340BL
ISSUE O

DATE 31 AUG 2016



NOTES:

- A. EXCEPT WHERE NOTED CONFORMS TO EIAJ SC91A.
- B. DOES NOT COMPLY EIAJ STD. VALUE.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- E. DIMENSION AND TOLERANCE AS PER ASME Y14.5-1994.

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